

Dual P-Channel 25-V (G-S) MOSFET

PRODUCT SUMMARY		
V_{DS} (V)	$r_{DS(on)}$ (Ω)	I_D (A)
- 30	0.023 at $V_{GS} = - 10$ V	- 7.6
	0.029 at $V_{GS} = - 6$ V	- 6.8

FEATURES

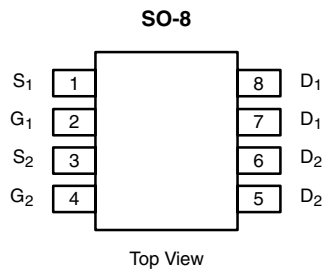
- TrenchFET[®] Power MOSFET
- 25 V V_{GS} Provides Extra Head Room for Safe Operation



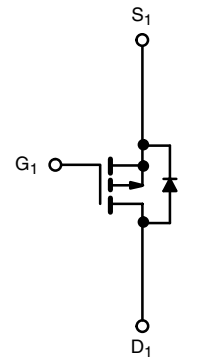
RoHS*
COMPLIANT

APPLICATIONS

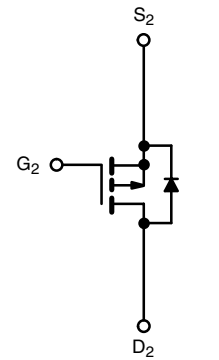
- Notebook
 - Load Switch
 - Battery Charger Switch



Ordering Information: Si4973DY-T1
Si4973DY-T1-E3 (Lead (Pb)-free)



P-Channel MOSFET



P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS $T_A = 25$ °C, unless otherwise noted				
Parameter	Symbol	10 sec	Steady State	Unit
Drain-Source Voltage	V_{DS}	- 30		V
Gate-Source Voltage	V_{GS}	± 25		
Continuous Drain Current ($T_J = 150$ °C) ^a	I_D	$T_A = 25$ °C	- 7.6	- 5.8
		$T_A = 70$ °C	- 6.1	- 4.6
Pulsed Drain Current	I_{DM}	- 30		A
Continuous Source Current (Diode Conduction) ^a	I_S	- 1.7	- 0.9	
Maximum Power Dissipation ^a	P_D	$T_A = 25$ °C	2.0	1.1
		$T_A = 70$ °C	1.3	0.7
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to 150		°C

THERMAL RESISTANCE RATINGS				
Parameter	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^a	R_{thJA}	$t \leq 10$ sec	45	62.5
		Steady State	85	110
Maximum Junction-to-Foot (Drain)	R_{thJF}	26	35	°C/W

Notes:

a. Surface Mounted on 1" x 1" FR4 Board.

* Pb containing terminations are not RoHS compliant, exemptions may apply.

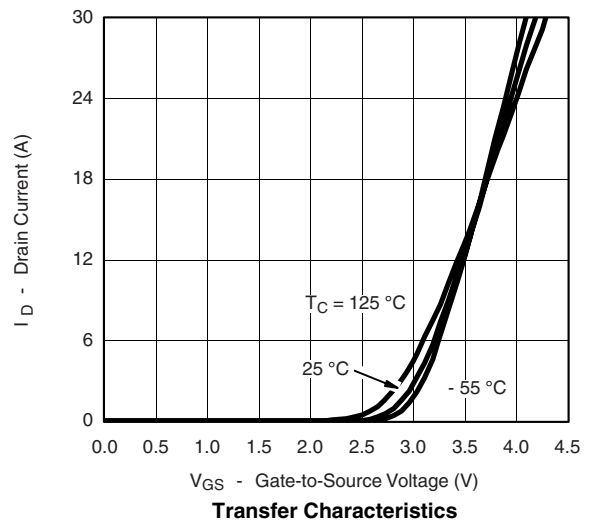
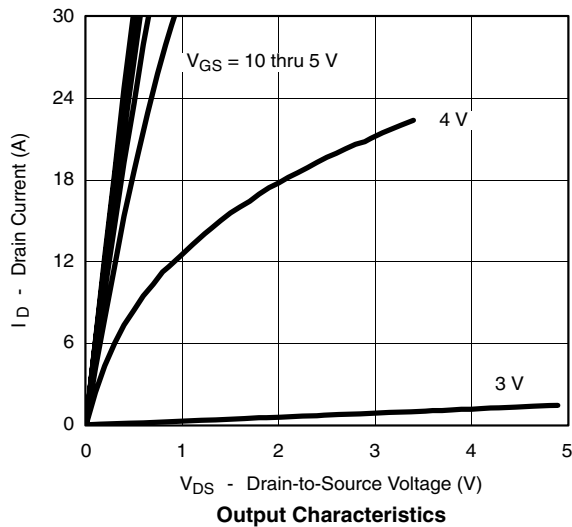
SPECIFICATIONS $T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted						
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Static						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\text{ }\mu\text{A}$	-1		-3	V
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			± 100	nA
		$V_{DS} = 0\text{ V}, V_{GS} = \pm 25\text{ V}$			± 200	
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -30\text{ V}, V_{GS} = 0\text{ V}$			-1	μA
		$V_{DS} = -30\text{ V}, V_{GS} = 0\text{ V}, T_J = 55\text{ }^\circ\text{C}$			-25	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} = -5\text{ V}, V_{GS} = -10\text{ V}$	-30			A
Drain-Source On-State Resistance ^a	$r_{DS(on)}$	$V_{GS} = -10\text{ V}, I_D = -7.6\text{ A}$		0.018	0.023	Ω
		$V_{GS} = -6\text{ V}, I_D = -6.8\text{ A}$		0.023	0.029	
Forward Transconductance ^a	g_{fs}	$V_{DS} = -10\text{ V}, I_D = -7.6\text{ A}$		22		S
Diode Forward Voltage ^a	V_{SD}	$I_S = -1.7\text{ A}, V_{GS} = 0\text{ V}$		-0.8	-1.2	V
Dynamic^b						
Total Gate Charge	Q_g	$V_{DS} = -15\text{ V}, V_{GS} = -10\text{ V}, I_D = -7.6\text{ A}$		37	56	nC
Gate-Source Charge	Q_{gs}		6			
Gate-Drain Charge	Q_{gd}		11			
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = -15\text{ V}, R_L = 15\text{ }\Omega$ $I_D \cong -1\text{ A}, V_{GEN} = -10\text{ V}, R_G = 6\text{ }\Omega$		10	15	ns
Rise Time	t_r		15	25		
Turn-Off Delay Time	$t_{d(off)}$		115	180		
Fall Time	t_f		90	140		
Source-Drain Reverse Recovery Time	t_{rr}		$I_F = -1.7\text{ A}, di/dt = 100\text{ A}/\mu\text{s}$		80	

Notes:

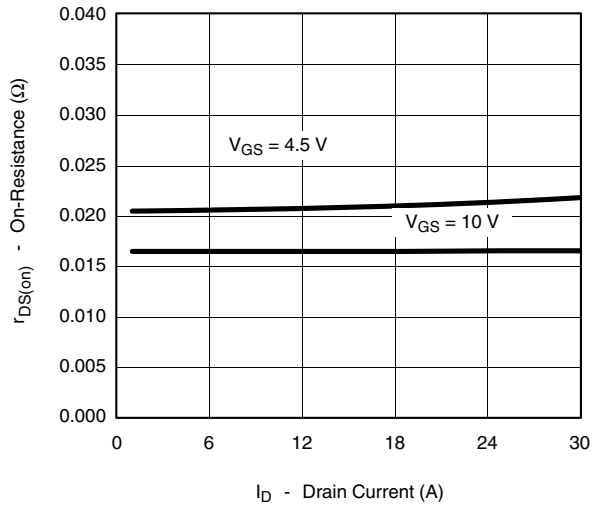
- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

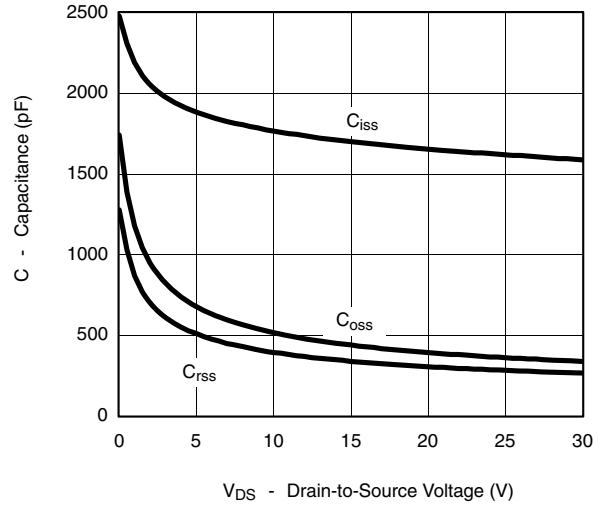
TYPICAL CHARACTERISTICS $25\text{ }^\circ\text{C}$ unless noted



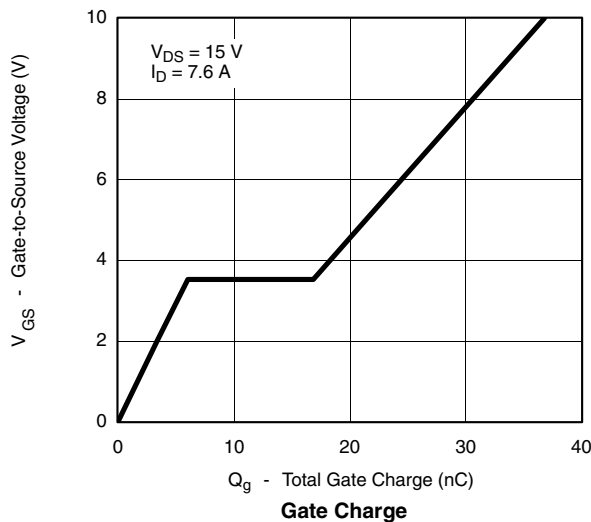
TYPICAL CHARACTERISTICS 25 °C unless noted



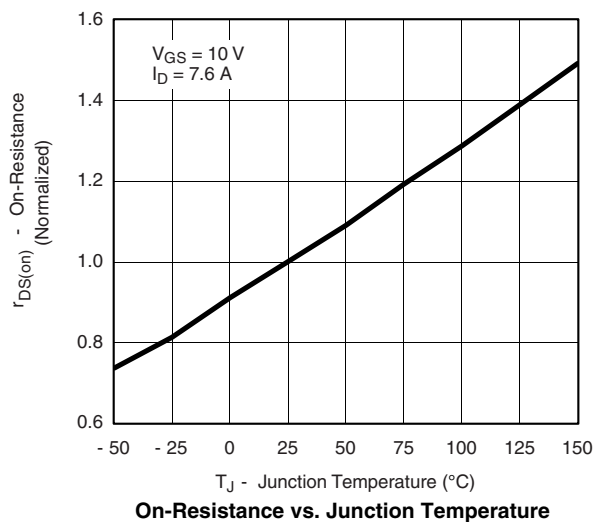
On-Resistance vs. Drain Current



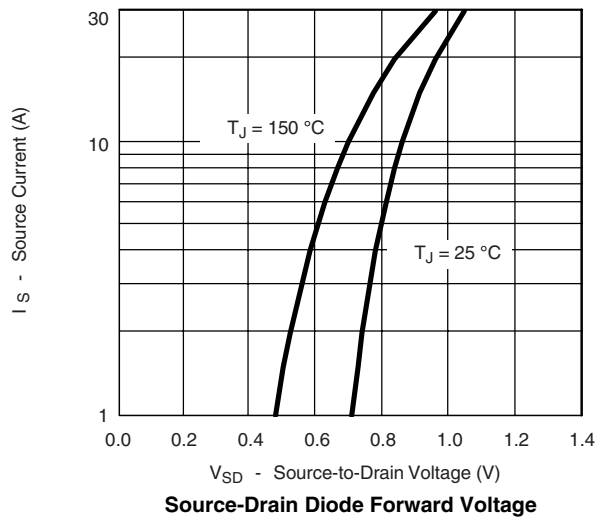
Capacitance



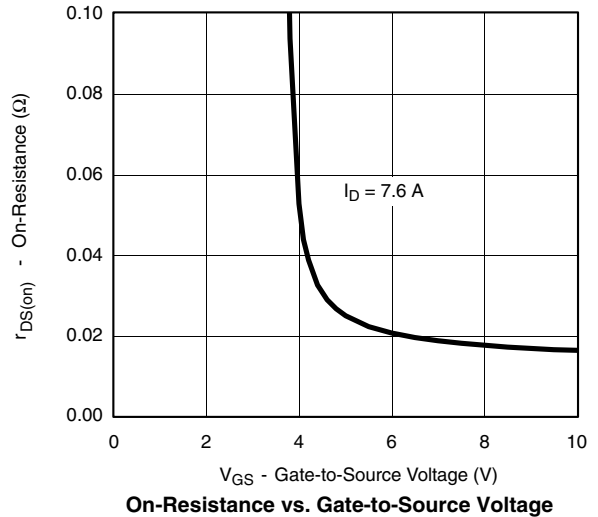
Gate Charge



On-Resistance vs. Junction Temperature

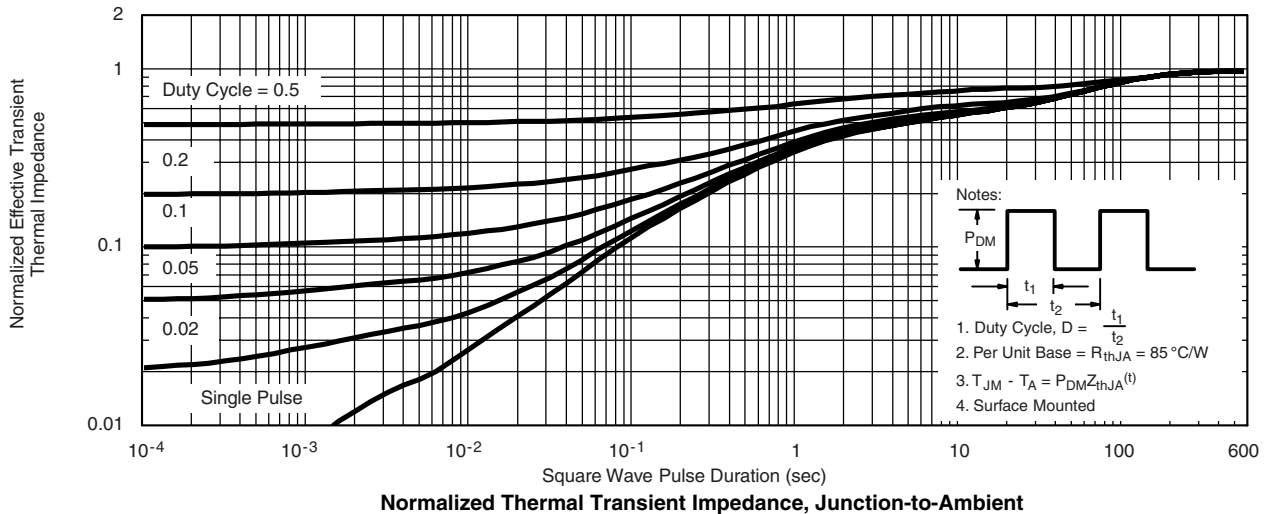
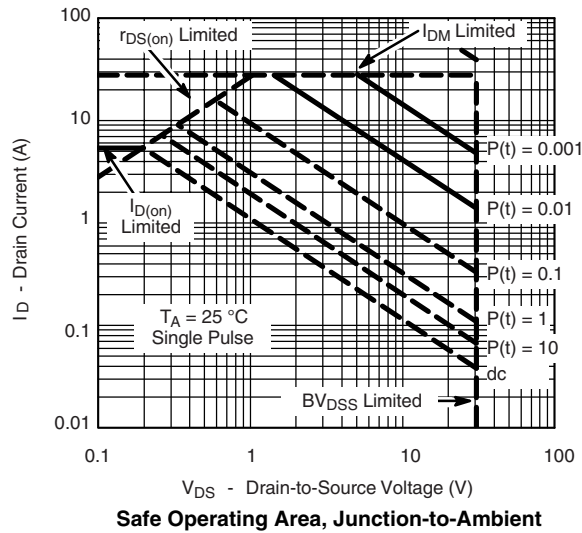
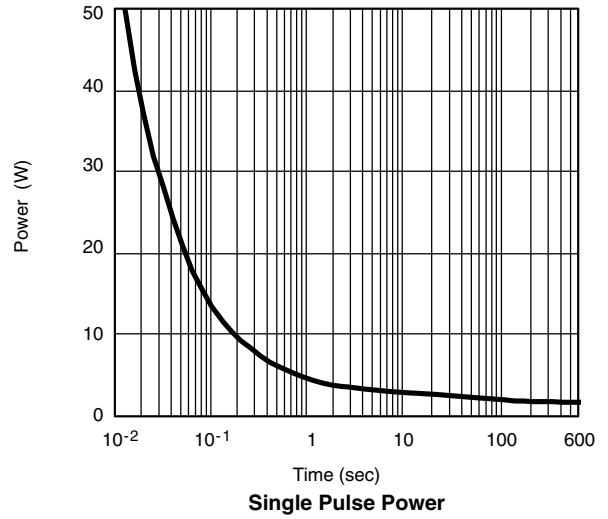
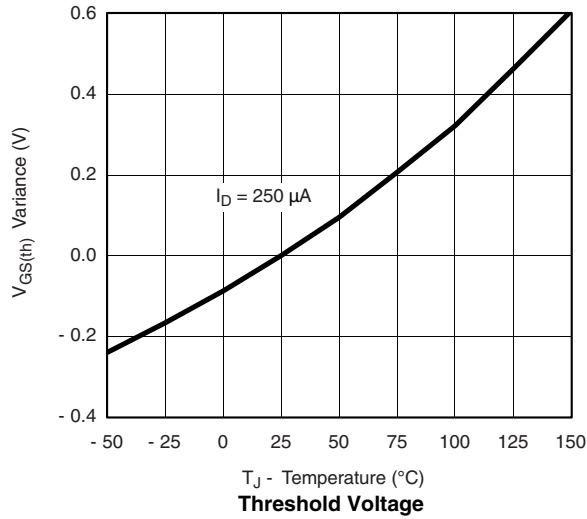


Source-Drain Diode Forward Voltage



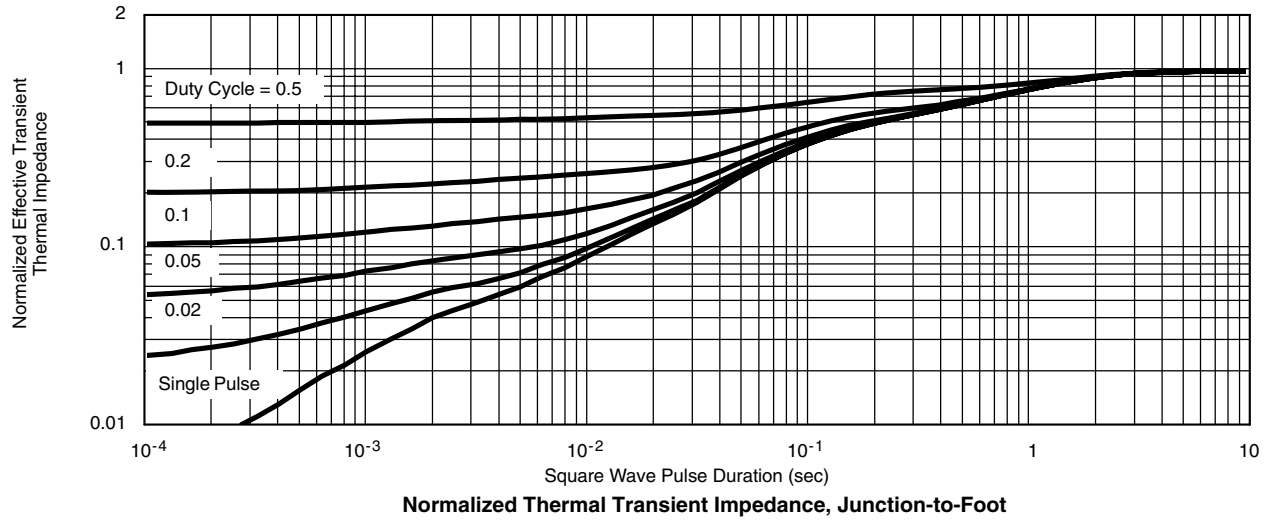
On-Resistance vs. Gate-to-Source Voltage

TYPICAL CHARACTERISTICS 25 °C unless noted





TYPICAL CHARACTERISTICS 25 °C unless noted



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